

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-11. (cancelled)

12. **(currently amended)** A process of lapping a second side of a wafer, which is provided at a first side thereof with a ultraviolet tape attached to said first side, said method comprising the steps of:

irradiating the ultraviolet tape attached to the first side of the wafer with ultraviolet light;
maintaining a lapping jig, on which the wafer is to be placed, at a temperature higher than a binder's melting temperature but lower than a deformation temperature of the ultraviolet tape;
applying the binder to an upper surface of the lapping jig;
bonding the first side of the wafer to the lapping jig via the binder;
placing the lapping jig having the wafer bonded thereto on a lapping plate;
lapping the second side of the wafer to cause the wafer to have a predetermined thickness;
and

removing the wafer from the lapping jig;

~~The method of claim 1,~~ wherein said irradiating step is performed before said lapping step.

13. (previously presented) The method of claim 12, wherein said irradiating step is performed before said bonding step.

14. (cancelled)

15. **(currently amended)** A method of processing a backside of a wafer, said method comprising the steps of:

attaching a ultraviolet tape to a front side of the wafer;
grinding the backside of the wafer to cause the wafer to have a first thickness;
irradiating the ultraviolet tape attached to the front side of the wafer with ultraviolet light;
maintaining a lapping jig at a temperature higher than a binder's melting temperature but lower than a deformation temperature of the ultraviolet tape;
applying the binder to an upper surface of the lapping jig;
bonding the front side of the wafer to the lapping jig via the binder;
placing the lapping jig having the wafer bonded thereto on a lapping plate;
lapping the backside of the wafer to cause the wafer to have a second thickness;
removing the wafer from the lapping jig; and
removing the ultraviolet tape from the wafer;
~~The method of claim 11,~~ wherein said irradiating step is performed before said lapping step.

16. (previously presented) The method of claim 15, wherein said irradiating step is performed before said bonding step.

17. **(cancelled)**

18. (previously presented) A method of processing a wafer, said method comprising the steps of:

attaching a ultraviolet tape to a first side of the wafer;
irradiating the ultraviolet tape with ultraviolet light to relieve adhesive stress of the ultraviolet tape;
lapping a second, opposite side of the wafer to reduce a thickness of the wafer; and
removing the ultraviolet tape from the wafer;

wherein said irradiating step is performed before said lapping step.

19. (previously presented) The method of claim 18, further comprising bonding the first side of the wafer to a lapping jig via a binder before said lapping and after said irradiating.

20. (previously presented) The method of claim 19, wherein, in said bonding step, the ultraviolet tape is bonded to the lapping jig via the binder.